NSN 5961-01-024-3757

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-024-3757 **Inclosure Material:** Metal **Overall Length:** 0.505 inches **Mounting Facility Quantity: Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.562 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 100.0 breakover voltage, dc **Current Rating Per Characteristic:** 16.00 amperes source cutoff current **Power Rating Per Characteristic:** 1.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 120.0 degrees celsius junction **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug **Specification Data:** 80131-release4957 professional/industrial association specification Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig:

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